

MProbe In-situ Thin film measurement

(typical configurations)

It is easy to be an expert with MProbe

Any translucent films can be measured quickly and reliably: Optical coatings, Oxides, Nitrides, Photoresists, Polymers, Semiconductors (Si, aSi, polySi), Compound Semiconductors (AlGaAs, InGaAs, CdTe, CIGS), Hard coatings (SiC, DLC), metal oxides, thin metal films and many more.

Thickness Range: 1 nm - 500µm Wavelength Range: 200nm -1700nm

Flexible integration: inside or outside the deposition chamber.

Outside: Optical heads are placed outside the windows and light is focused on the sample. Optical system is customized to fit the chamber design.

Inside: Reflectance probe is welded with vacuum flange (feedthru) and placed above the sample.

Real time measurement and analysis. No moving parts, parallel (CCD or PDA) data acquisition, fast measurement and trend-chart data display.

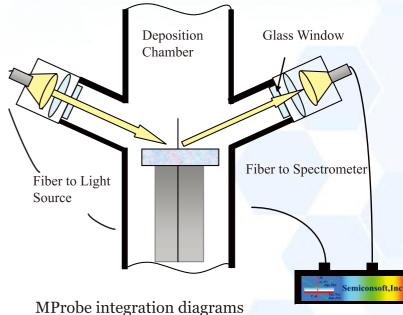
Extensive materials library (500+ materials) - new materials easily added. Support of parameterized materials: Cauchy, Tauc-Lorentz, Cody-Lorentz, EMA and many more....

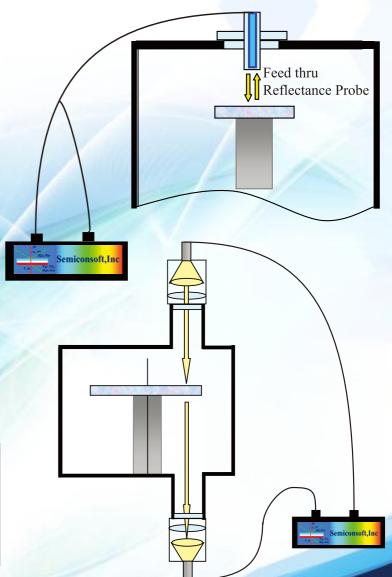
Control software integration: Easy integration with external system using TCP Modbus or OPC automation interface. Programmable hardware triggers (5V TTL).

Measured parameters: thickness, optical constants, surface roughness. Additional: Color coordinates (CIE), bandgap, free carriers/conductivity

User friendly and powerful: Easy measurement and analysis set-up. Background and scaling correction, linked layers and materials. Offline data analysis: simulation & sensitivity analysis, multisample measurements, production batch processing.

Precision	0.01nm or 0.01%
Accuracy	0.2% or 1 nm
Stability	0.02nm or 0.03%
Spot Size	3 mm typical (depends on configuration)
Sample Size	from 4 mm
Measurement	< 1 s (20ms to 200ms typical)





In-Situ System models VIS **USVISSR HRVIS NIR VISNIR UVVISNIR** 100nm $1\mu m$ $10\mu m$ $100 \mu m$ 1_mm 1nm 10nm Model Wavelength Spectrometer/Detector/Light Thickness range* range source Spectrometer F4/Si 3600 pixels/ 15 nm to 20 µm VIS 400-1100 nm Tungsten - Halogen light source (option:up to 50 µm) Spectrometer F4/ Si CCD 3600 pix-**UVVisF** 200-900 nm els/ Flash Xe light source 1 nm to 20 µm (option:up to 50 µm) **HRVIS** HR Spectrometer F4/Si 3600 pix-700-1000 nm els/ Tungsten - Halogen light source | 1 μm to 400 μm Transmission Spectrometer (TVG) **NIR** 900-1700nm F2/512 InGaAs/Tungsten-Halogen 100 nm-200 μm light source **VISNIR** Spectrometer F4 Si CCD 3600 400-1700 nm pixels(Vis channel);Transmission 15 nm to 200 μm Spectrometer (TVG)F2/512 InGaAs PDA(NIR channel) Tungsten-Halogen light source Spectrometer F4 Si CCD 3600 **UVVIS-**200 -1700 nm pixels(Vis channel); Transmission **NIR** (TVG) F2/512 InGaA (NIR channel) 1 nm -200 μm Deuterium & Tungsten-Halogen light source XT Transmission Spectrometer (TVG) 1590nm -1650nm F2/512 InGaAs/Tungsten-Halogen 10 μm-1 mm

light source

^{*} T, n & k measurement in 40nm - $5\mu\text{m}$ thickness range Other configuration are available. OEM inquiries and custom development projects are welcome. One year limited warranty on labor and materials for all system.